

General Description

- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- ESD protected

Applications

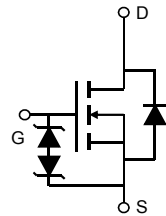
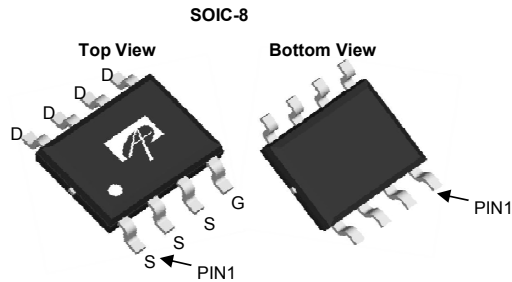
- High efficiency power supply
- Secondary synchronus rectifier

Product Summary

V_{DS}	60V
I_D (at $V_{GS}=10V$)	13.5A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 9.8mΩ
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	< 13.5mΩ

Typical ESD protection **HBM Class 2**

100% UIS Tested
100% Rg Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AO4264E	SO-8	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	13.5	A
	$T_A=70^\circ\text{C}$	10.5	
Pulsed Drain Current ^C	I_{DM}	54	A
Avalanche Current ^C	I_{AS}	17	A
Avalanche energy $L=0.3\text{mH}$ ^C	E_{AS}	43	mJ
V_{DS} Spike ^G	V_{SPIKE}	72	V
	$10\mu\text{s}$		
Power Dissipation ^B	P_D	3.1	W
	$T_A=70^\circ\text{C}$	2.0	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A,D}		59	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.4	1.8	2.4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=13.5\text{A}$ $T_J=125^{\circ}\text{C}$		8 12.5	9.8 15.0	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=11.5\text{A}$		10.5	13.5	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=13.5\text{A}$		48		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=30\text{V}$, $f=1\text{MHz}$		1100		pF
C_{oss}	Output Capacitance			300		pF
C_{rss}	Reverse Transfer Capacitance			28		pF
R_g	Gate resistance	$f=1\text{MHz}$	0.6	1.2	2.0	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $I_D=13.5\text{A}$		14.5	25	nC
$Q_g(4.5\text{V})$	Total Gate Charge			7	13	nC
Q_{gs}	Gate Source Charge			2.5		nC
Q_{gd}	Gate Drain Charge			3.5		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=30\text{V}$, $R_L=2.2\Omega$, $R_{GEN}=3\Omega$		6.5		ns
t_r	Turn-On Rise Time			3.5		ns
$t_{D(off)}$	Turn-Off DelayTime			22		ns
t_f	Turn-Off Fall Time			3		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=13.5\text{A}$, $di/dt=500\text{A}/\mu\text{s}$		18.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=13.5\text{A}$, $di/dt=500\text{A}/\mu\text{s}$		59		nC

- A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.
- B. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using $\leq 10\text{s}$ junction-to-ambient thermal resistance.
- C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^{\circ}\text{C}$.
- D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-ambient thermal impedance which is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.
- G. The spike duty cycle 5% max, limited by junction temperature $T_J(MAX)=125^{\circ}\text{C}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

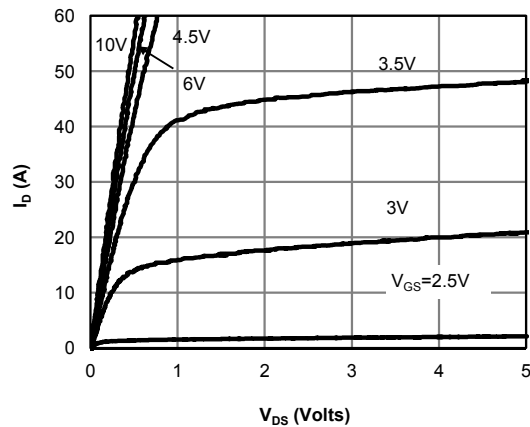


Figure 1: On-Region Characteristics (Note E)

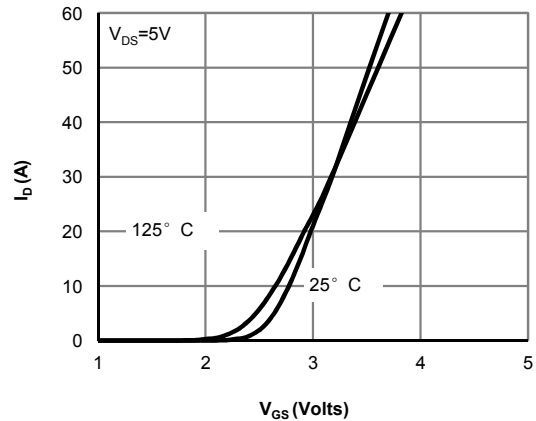


Figure 2: Transfer Characteristics (Note E)

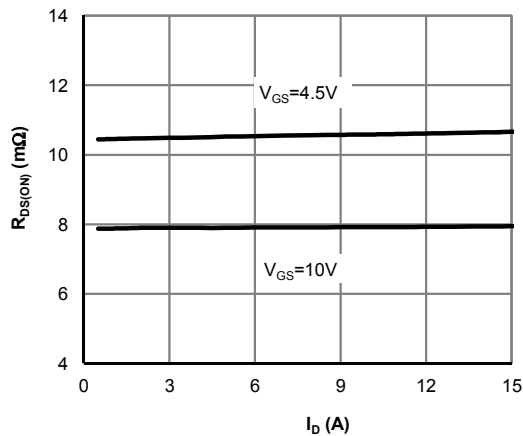


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

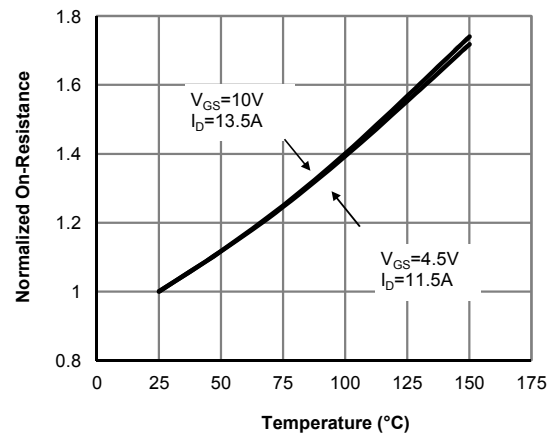


Figure 4: On-Resistance vs. Junction Temperature (Note E)

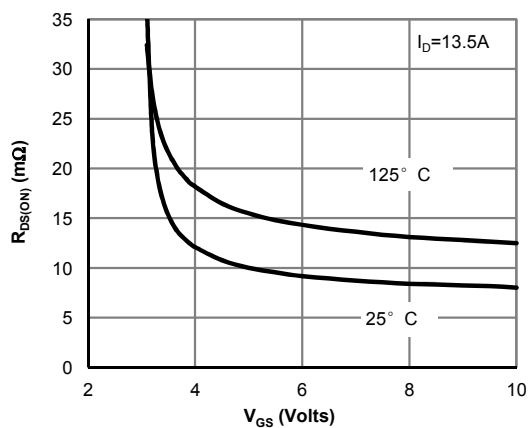


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

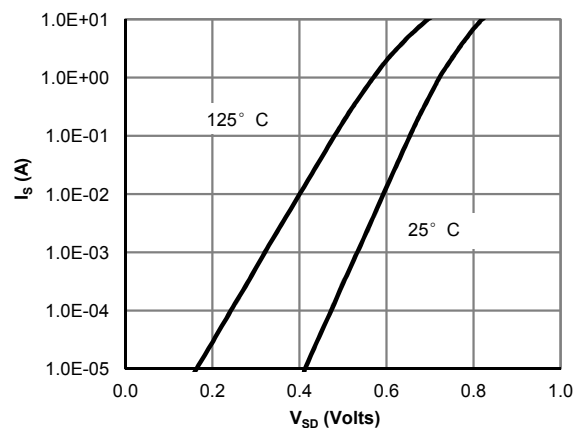


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

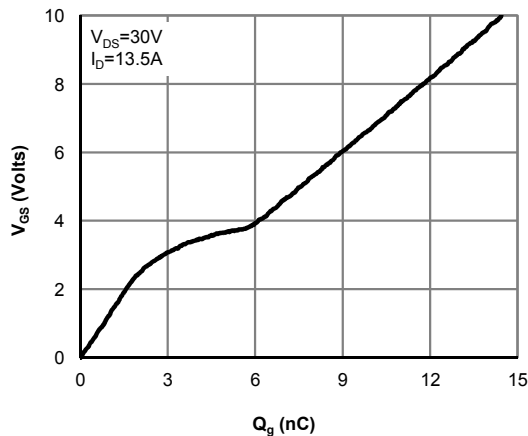


Figure 7: Gate-Charge Characteristics

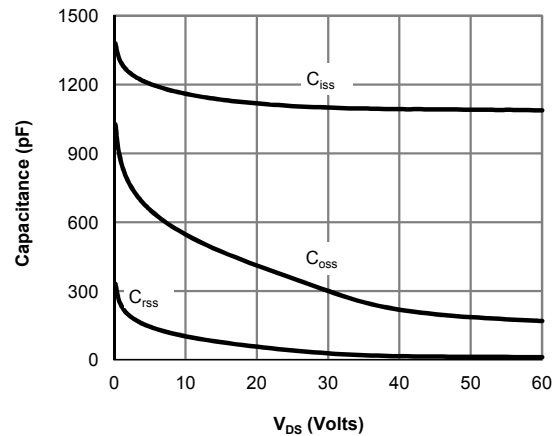


Figure 8: Capacitance Characteristics

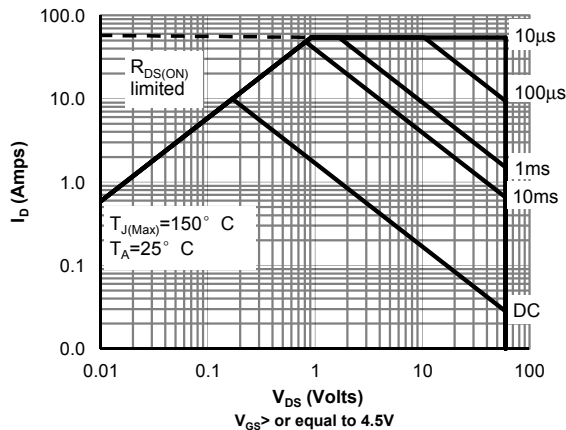


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

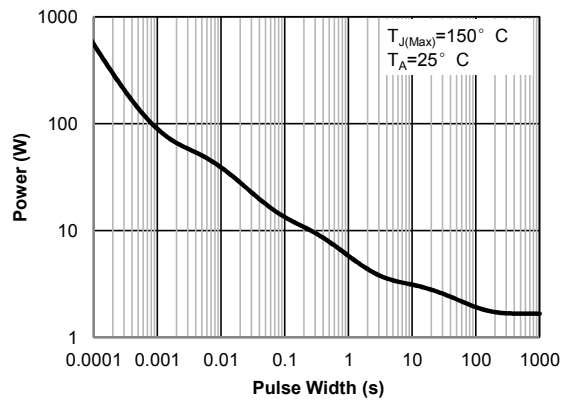


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

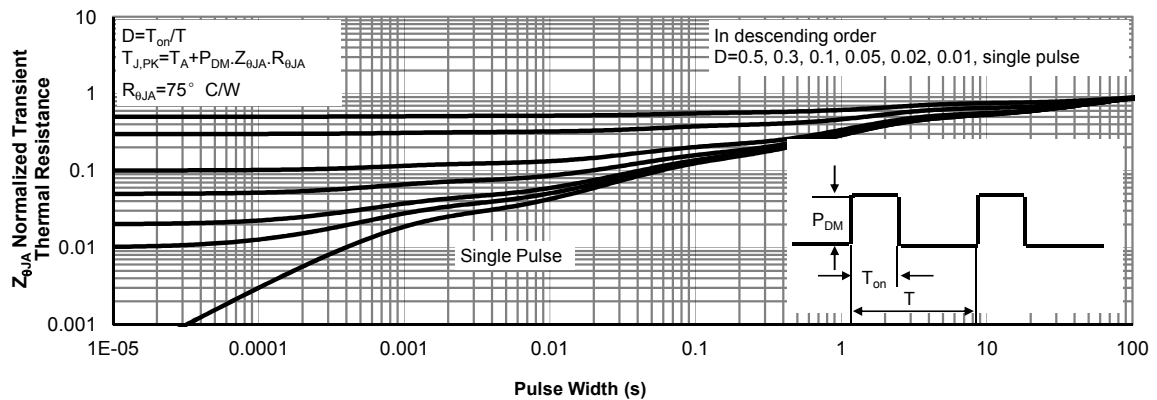


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

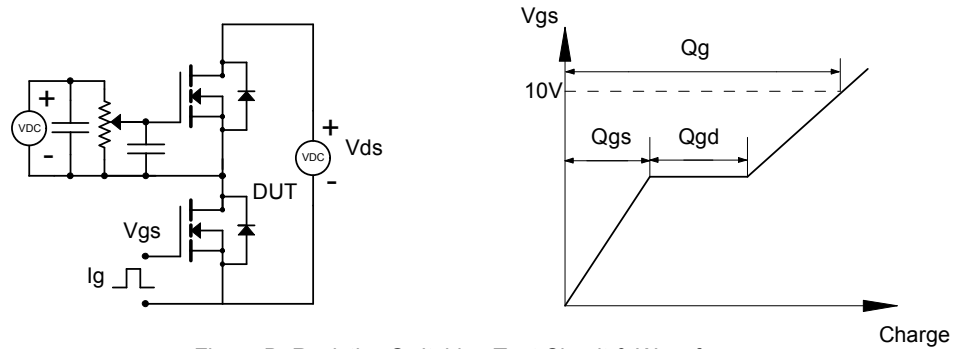


Figure B: Resistive Switching Test Circuit & Waveforms

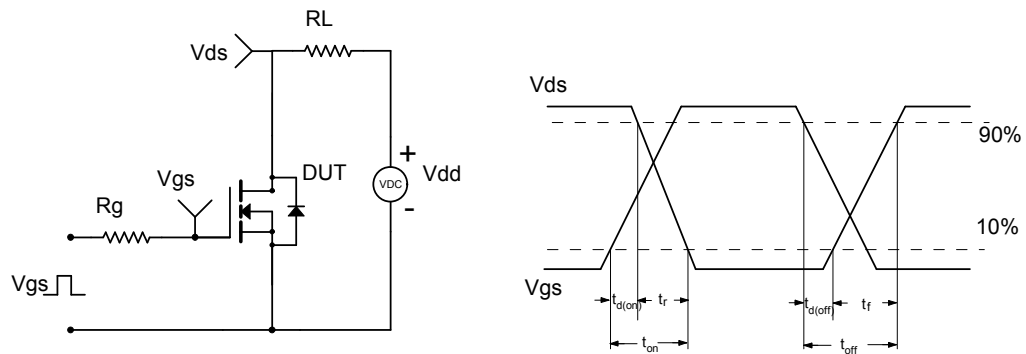


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

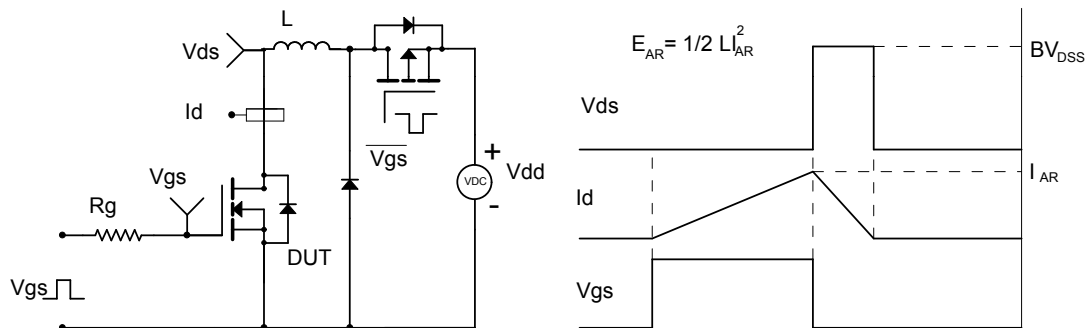


Figure D: Diode Recovery Test Circuit & Waveforms

